

Monday, September 15

12:55-16:45 Short Course 1(301, 3rd Floor), Short Course 2 (302, 3rd Floor)
17:00-18:00 Special Talk Session (302, 3rd Floor)
18:00-19:30 Welcome Reception (315, 3rd Floor)

Tuesday, September 16

9:00-11:35 Opening and Plenary Session (301-304)											
Lunch											
Room A (301, 3rd Floor)	Room B (302, 3rd Floor)	Room C (303, 3rd Floor)	Room D (304, 3rd Floor)	Room E (311, 3rd Floor)	Room F (312, 3rd Floor)	Room G (313, 3rd Floor)	Room H (314, 3rd Floor)	Room J (411+412, 4th Floor)	Room K (413, 4th Floor)	Room M (414+415, 4th Floor)	Room N (416+417, 4th Floor)
13:30-15:15 [A-1] CFET Technology	13:30-15:00 [B-1] 3D NAND Flash Memory	13:30-15:00 [C-1] Power and Sensing Circuits	13:30-15:15 [D-1] Spintronics/Quantum Materials/Reservoir Computing	13:30-15:00 [E-1] Photovoltaics	13:30-15:00 [F-1] Organic/Inorganic Hybrid Electronics	13:30-15:00 [G-1] Integrated Photonics	13:30-15:00 [H-1] Group IV Materials	13:30-15:00 [J-1] 3D Integration	13:30-15:00 [K-1] Growth	13:30-15:00 [M-1] SiC Materials and Processes	13:30-15:00 [N-1] Oxide Semiconductor Devices 1
Coffee Break											
15:30-17:00 [A-2] Threshold Voltage Control	15:30-17:00 [B-2] In-Memory and Unconventional Computing 1	15:30-16:45 [C-2] Device Circuit Co-Design		15:30-16:45 [E-2] Thermoelectric Devices and Materials	15:30-17:00 [F-2] Organic Electronics	15:30-17:00 [G-2] Light Sources	15:30-16:45 [H-2] Wide Bandgap and Oxide Materials I	15:30-17:00 [J-2] Advanced Devices	15:30-17:00 [K-2] Characterization I	15:30-17:00 [M-2] THz and High-speed Devices	15:15-17:00 [N-2] Oxide Semiconductor Devices 2

Wednesday, September 17

Room A (301, 3rd Floor)	Room B (302, 3rd Floor)	Room C (303, 3rd Floor)	Room D (304, 3rd Floor)	Room E (311, 3rd Floor)	Room F (312, 3rd Floor)	Room G (313, 3rd Floor)	Room H (314, 3rd Floor)	Room J (411+412, 4th Floor)	Room K (413, 4th Floor)	Room M (414+415, 4th Floor)	Room N (416+417, 4th Floor)
9:00-10:30 [A-3] Process Technology and Characterization	9:00-10:15 [B-3] Ferroelectric Devices				9:00-10:15 [F-3] Oscillators and Interface Circuits	9:00-10:15 [G-3] Advanced Photonic Designs	9:00-10:15 [H-3] Wide Bandgap and Oxide Materials II	9:45-10:15 [J-3] 3D Integration/Novel Materials	9:00-10:15 [K-3] Device I	9:00-10:15 [M-3] Ga2O3 Power Devices	9:00-10:15 [N-3] Oxide Semiconductor Devices 3
Coffee Break											
10:45-12:15 [A-4] Cryo CMOS and SOI Technology	10:45-12:15 [B-4] Ferroelectric Memory Devices			10:45-12:15 [E-4] ReRAM	10:45-12:00 [F-4] AI Computing Circuits	10:45-11:45 [G-4] UV Photonics	10:45-12:00 [H-4] Characterization and Device Applications	10:45-12:00 [J-4] 3D Integration-Packaging/Sensors/Novel Materials	10:45-12:00 [K-4] Characterization II	10:45-12:00 [M-4] GaN, Ga2O3 Processes	10:45-12:00 [N-4] Oxide Semiconductor Devices 4
Lunch											
13:30-14:00 [SO-PS-01] Short Oral Presentation	13:30-14:32 [SO-PS-02] Short Oral Presentation			13:30-13:42 [SO-PS-06] Short Oral Presentation	13:30-13:56 [SO-PS-07] Short Oral Presentation	13:30-14:10 [SO-PS-05] Short Oral Presentation	14:00-14:28 [SO-PS-11] Short Oral Presentation	14:15-14:31 [SO-PS-03] Short Oral Presentation	13:30-14:12 [SO-PS-08] Short Oral Presentation	13:30-14:20 [SO-PS-04] Short Oral Presentation	13:30-14:10 [SO-PS-10] Short Oral Presentation
				14:14-14:28 [SO-PS-09] Short Oral Presentation	14:15-14:35 [SO-PS-12] Short Oral Presentation						
Coffee Break											

Thursday, September 18

Room A (301, 3rd Floor)	Room B (302, 3rd Floor)	Room C (303, 3rd Floor)	Room D (304, 3rd Floor)	Room E (311, 3rd Floor)	Room F (312, 3rd Floor)	Room G (313, 3rd Floor)	Room H (314, 3rd Floor)	Room J (411+412, 4th Floor)	Room K (413, 4th Floor)	Room M (414+415, 4th Floor)	Room N (416+417, 4th Floor)
9:00-10:30 [A-5] CFET Technology and Self-heating	9:00-10:15 [B-5] Ferroelectric FET			9:00-10:30 [E-5] Qubit Technology	9:00-10:15 [F-5] Highly Sensitive Devices for Chem/Bio Detection 1	9:00-10:00 [G-5] Photonic Computing	9:00-10:15 [H-5] Low Dimensional Materials I	9:00-10:15 [J-5] In-Memory and Unconventional Computing 2	9:00-10:15 [K-5] Device II	9:00-10:15 [M-5] Emerging Materials and Devices	09:00-10:00 [N-5] Ferroelectric Memories and Gate Stack
Coffee Break											
10:45-12:00 [A-6] Integration Technology on Si Wafer	10:45-12:15 [B-6] Emerging Memory Devices, and DRAM			10:45-12:00 [E-6] Qubit Systems	10:45-12:00 [F-6] Highly Sensitive Devices for Chem/Bio Detection 2	10:45-11:45 [G-6] Materials for Photodetector	10:45-11:45 [H-6] Low Dimensional Materials II	10:45-12:15 [J-6] Emerging Memory Devices, and DRAM	10:45-11:45 [K-6] Characterization III	10:45-12:00 [M-6] III-V High-frequency and Power Devices	10:15-12:15 [N-6] Group-IV, III-V based Thin-film Growth, and Device Application
Lunch											
13:30-14:45 [A-7] 2D Material Integration	13:30-14:45 [B-7] Ferroelectric Materials			13:30-14:45 [E-7] Energy Related Materials	13:30-14:45 [F-7] Bio/Medical Electronics		13:30-14:45 [H-7] Advanced Materials and Thin Films		13:30-14:30 [K-7] Device III	13:30-14:45 [M-7] Technologies for GaN HEMTs	
Coffee Break											
15:15-16:15 [A-8] Vertical FET and New Devices	15:15-16:30 [B-8] Ferroelectric Memory Materials								15:15-16:00 [K-8] Device IV	15:15-16:30 [M-8] Si Materials and Devices	

Area Scope	Area 1: Advanced CMOS: Material Science / Process Engineering / Device Technology
	Area 2: Advanced and Emerging Memories / New Applications
	Area 3: Heterogeneous and 3D Integration / Interconnect / MEMS
	Area 4: Power / High-speed Devices and Materials
	Area 5: Photonics: Devices / Integration / Related Technology
	Area 6: Energy Harvesting and Converting Devices and Materials

Area Scope	Area 7: Organic / Molecular / Bio-electronics
	Area 8: Low Dimensional Devices and Materials
	Area 9: Novel Functional / Quantum / Spintronic Devices and Materials
	Area 10: Thin Film Electronics: Oxide / Non-single Crystalline / Novel Process
	Area 11: Advanced Materials: Synthesis / Crystal Growth / Characterization
	Area12: Advanced and Innovative Circuits / Systems Interacting with Devices and Materials